1-Bit Dual-Supply Inverting Level Translator

The NLSV1T240 is a 1-bit configurable dual-supply voltage level translator. The input A_n and output B_n ports are designed to track two different power supply rails, V_{CCA} and V_{CCB} respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input A_n to the output B_n port.

Features

- Wide V_{CCA} and V_{CCB} Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V_{CCA} and V_{CCB} Sequencing
- Outputs at 3-State until Active V_{CC} is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V_{CCB} at GND
- Ultra-Small Packaging: 1.2 mm x 1.0 mm UDFN6
- This is a Pb-Free Device

Typical Applications

• Mobile Phones, PDAs, Other Portable Devices

Important Information

• ESD Protection for All Pins: Human Body Model (HBM) > 2000 V

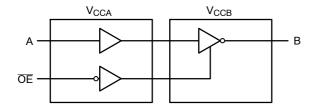


Figure 1. Logic Diagram



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UDFN6 MU SUFFIX CASE 517AA

MARKING DIAGRAM

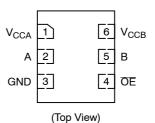


3 = Specific Device Code

M = Date Code

= Pb-Free Package

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping [†]
NLSV1T240MUTBG	UDFN6 (Pb-Free)	3000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PIN ASSIGNMENT

PIN	FUNCTION
V _{CCA}	Input Port DC Power Supply
V _{CCB}	Output Port DC Power Supply
GND	Ground
Α	Input Port
В	Output Port
ŌĒ	Output Enable

TRUTH TABLE

In	Outputs	
ŌĒ	Α	В
L	L	Н
L	Н	L
Н	X	3-State

MAXIMUM RATINGS

Symbol	Rating		Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage		-0.5 to +5.5		V
VI	DC Input Voltage	Α	-0.5 to +5.5		V
V _C	Control Input	ŌĒ	-0.5 to +5.5		V
Vo	DC Output Voltage (Power Down)	В	-0.5 to +5.5	$V_{CCA} = V_{CCB} = 0$	٧
	(Active Mode)	В	-0.5 to +5.5		٧
	(Tri-State Mode)	В	-0.5 to +5.5		V
lık	DC Input Diode Current		-20	V _I < GND	mA
lok	DC Output Diode Current		-50	V _O < GND	mA
I _O	DC Output Source/Sink Current		±50		mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin		±100		mA
I _{GND}	DC Ground Current per Ground Pin		±100		mA
T _{STG}	Storage Temperature		-65 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CCA} , V _{CCB}	Positive DC Supply Voltage		0.9	4.5	V
VI	Bus Input Voltage		GND	4.5	V
V _C	Control Input	ŌĒ	GND	4.5	V
V _{IO}	Bus Output Voltage (Power Down Mode)	В	GND	4.5	V
	(Active Mode)	В	GND	V _{CCB}	V
	(Tri-State Mode)	В	GND	4.5	V
T _A	Operating Temperature Range		-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V _I , from 30% to 70% of V _{CC} ; V _{CC} = 3.3 V \pm 0.3 V		0	10	nS

DC ELECTRICAL CHARACTERISTICS

					-40°C to	o +85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Uni
V _{IH}	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	-	V
	(A, \overline{OE})		2.7 – 3.6	1	2.0	-	
			2.3 – 2.7		1.6	-	
			1.4 – 2.3	1	0.65 * V _{CCA}	-	
			0.9 – 1.4	1	0.9 * V _{CCA}	-	
V _{IL}	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	0.8	٧
	(A, \overline{OE})		2.7 – 3.6		_	0.8	
			2.3 – 2.7		_	0.7	
			1.4 – 2.3		_	0.35 * V _{CCA}	
			0.9 – 1.4	1	-	0.1 * V _{CCA}	
V _{OH}	Output HIGH Voltage	I _{OH} = -100 μA; V _I = V _{IL}	0.9 – 4.5	0.9 – 4.5	V _{CCB} - 0.2	_	٧
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IL}$	0.9	0.9	0.75 * V _{CCB}	_	
		I _{OH} = -2 mA; V _I = V _{IL}	1.4	1.4	1.05	_	
		I _{OH} = -6 mA; V _I = V _{IL}	1.65	1.65	1.25	_	
			2.3	2.3	2.0	_	
		I _{OH} = -12 mA; V _I = V _{IL}	2.3	2.3	1.8	_	
			2.7	2.7	2.2	_	
		I _{OH} = -18 mA; V _I = V _{IL}	2.3	2.3	1.7	_	
			3.0	3.0	2.4	_	
		I _{OH} = -24 mA; V _I = V _{IL}	3.0	3.0	2.2	_	
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	_	0.2	V
02		I _{OL} = 0.5 mA; V _I = V _{IH}	1.1	1.1	_	0.3	
		I _{OL} = 2 mA; V _I = V _{IH}	1.4	1.4	_	0.35	
		I _{OL} = 6 mA; V _I = V _{IH}	1.65	1.65	_	0.3	
		I _{OL} = 12 mA; V _I = V _{IH}	2.3	2.3	_	0.4	
		7 1 111	2.7	2.7	_	0.4	
		I _{OL} = 18 mA; V _I = V _{IH}	2.3	2.3	_	0.6	
		7 1 111	3.0	3.0	_	0.4	
		I _{OL} = 24 mA; V _I = V _{IH}	3.0	3.0	_	0.55	
l _l	Input Leakage Current	$V_I = V_{CCA}$ or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μA
I _{OFF}	Power-Off Leakage Current	OE = 0 V	0 0.9 – 4.5	0.9 – 4.5	-1.0 -1.0	1.0	μA
I _{CCA}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	_	1.0	μA
I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	1.0	μÆ
CCA + ICCB	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	_	2.0	μÆ
ΔI_{CCA}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μA
ΔI_{CCB}	Increase in I_{CC} per Input Voltage, Other Inputs at V_{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μA
I _{OZ}	I/O Tri-State Output Leakage Current	$T_A = 25^{\circ}C, \overline{OE} = 0 \text{ V}$	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μA

TOTAL STATIC POWER CONSUMPTION (I_{CCA} + I_{CCB})

_			•	•	-40°C to	o +85°C			•		
	V _{CCB} (V)										
	4.5			.3	2.8		2.8 1.8		.8 0.9		
V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

 $NOTE: \quad \text{Connect ground before applying supply voltage V_{CCA} or V_{CCB}. This device is designed with the feature that the power-up}$ sequence of $V_{\mbox{\footnotesize{CCA}}}$ and $V_{\mbox{\footnotesize{CCB}}}$ will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

				-40°C to +85°C									
							V _{CC}	_B (V)					
			4	.5	3	.3	2	.8	1	.8	1.	.2	
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation	4.5		1.6		1.8		2.0		2.1		2.3	nS
t _{PHL} (Note 1)	Delay,	3.3		1.7		1.9		2.1		2.3		2.6	
(Note 1)	A to B	2.8		1.9		2.1		2.3		2.5		2.8	
		1.8		2.1		2.4		2.5		2.7		3.0	
		1.2		2.4		2.7		2.8		3.0		3.3	
t _{PZH} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PZL} (Note 1)	Enable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{PHZ} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PLZ} (Note 1)	Disable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{OSHL} ,	Output to Output Skew,	4.5		0.15		0.15		0.15		0.15		0.15	nS
t _{OSLH} (Note 1)		3.3		0.15		0.15		0.15		0.15		0.15	
(Note 1)	Time	2.5		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

^{1.} Propagation delays defined per Figure 2.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C _{IN}	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C _{I/O}	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	5.0	pF

Typical values are at T_A = +25°C.
 C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC(operating)} ≅ C_{PD} x V_{CC} x f_{IN} where I_{CC} = I_{CCA} + I_{CCB}.

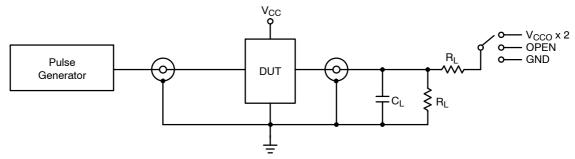


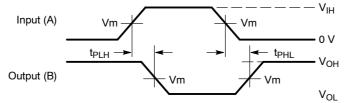
Figure 2. AC (Propagation Delay) Test Circuit

Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PLZ} , t _{PZL}	V _{CCO} x 2
t _{PHZ} , t _{PZH}	GND

 C_L = 15 pF or equivalent (includes probe and jig capacitance)

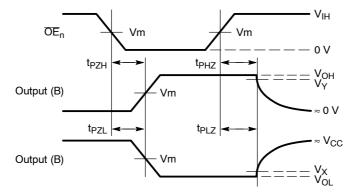
 $R_L = 2 k\Omega$ or equivalent

 Z_{OUT} of pulse generator = 50 Ω



Waveform 1 - Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



Waveform 2 - Output Enable and Disable Times

 t_{R} = t_{F} = 2.0 ns, 10% to 90%; f = 1 MHz; t_{W} = 500 ns

Figure 3. AC (Propagation Delay) Test Circuit Waveforms

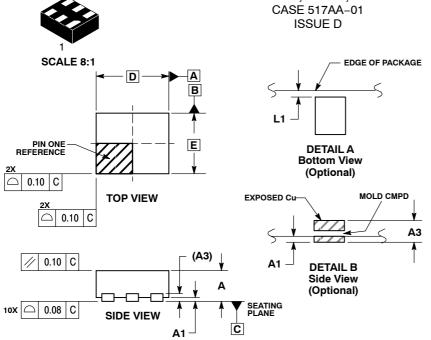
		V _{CC}						
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V			
V _{mA}	V _{CCA} /2							
V _{mB}	V _{CCB} /2							
V _X	V _{OL} x 0.1							
V _Y	V _{OH} x 0.9							

6X **b**

0.10 С A B

С 0.05

NOTE 3



5X L

е

BOTTOM VIEW

UDFN6, 1.2x1.0, 0.4P

DATE 03 SEP 2010

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 mm FROM TERMINAL.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS						
DIM	MIN	MAX					
Α	0.45	0.55					
A1	0.00	0.05					
А3	0.127	REF					
b	0.15	0.25					
D	1.20	BSC					
Е	1.00	BSC					
е	0.40	BSC					
L	0.30	0.40					
L1	0.00	0.15					
L2	0.40	0.50					

GENERIC MARKING DIAGRAM*

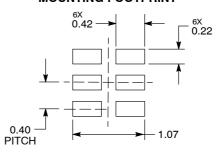


= Specific Device Code Х

= Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	6 PIN UDFN, 1.2X1.0, 0.4P		PAGE 1 OF 1

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MAX3371ELT+T NLSX3013BFCT1G NLV7WBD3125USG NLSX3012DMR2G 74AVCH1T45FZ4-7 NLVSV1T244MUTBG
74AVC1T45GS-Q100H CLVC16T245MDGGREP MC10H124FNG CAVCB164245MDGGREP CD40109BPWR MC10H350FNG
MC10H125FNG MC100EPT21MNR4G MC100EP91DWG NLSX3018MUTAG NLSV2T244MUTAG NLSX3013FCT1G
NLSX5011AMX1TCG PCA9306USG SN74GTL1655DGGR SN74AVCA406LZQSR NLSX4014DTR2G NLSX3018DTR2G
LTC1045CSW#PBF LTC1045CN#PBF SY100EL92ZG 74AXP1T34GMH 74AXP1T34GNH LSF0204DPWR PI4ULS3V204LE
ADG3245BRUZ-REEL7 ADG3123BRUZ ADG3245BRUZ ADG3246BCPZ ADG3308BCPZ-REEL ADG3233BRJZ-REEL7
ADG3233BRMZ